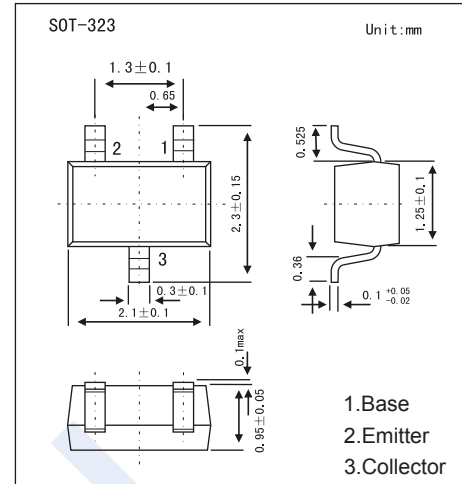


NPN Transistors

MMST3904 (KMST3904)

■ Features

- Epitaxial planar die construction
- Complementary to MMST3906



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	60	V
Collector - Emitter Voltage	V_{CE0}	40	
Emitter - Base Voltage	V_{EB0}	5	
Collector Current - Continuous	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _C = 100 μ A, I _E = 0	60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 10 mA, I _B = 0	40			
Emitter - base breakdown voltage	V _{EBO}	I _E = 100 μ A, I _C = 0	5			
Collector-base cut-off current	I _{CBO}	V _{CB} = 60 V, I _E = 0			60	nA
Collector-emitter cut-off current	I _{CEO}	V _{CE} = 40 V, I _B =0			500	
Collector-emitter cut-off current	I _{CEx}	V _{CE} =30V, V _{BE(off)} =-3V			50	
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =10 mA, I _B =1mA (Note.1)			0.25	V
		I _C = 50 mA, I _B = 5mA (Note.1)			0.3	
Base - emitter saturation voltage	V _{BE(sat)}	I _C =10 mA, I _B =1mA (Note.1)			0.85	
		I _C = 50 mA, I _B = 5mA (Note.1)			0.95	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = 1V, I _C = 0.1mA	40			
	h _{FE(2)}	V _{CE} = 1V, I _C = 1mA	70			
	h _{FE(3)}	V _{CE} = 1V, I _C = 10mA	100		30	
	h _{FE(4)}	V _{CE} = 1V, I _C = 50mA	60			
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V I _C =10mA, I _{B1} =1mA			35	nS
Rise time	t _r				35	
Storage time	t _s	V _{CC} =30V, I _C =10mA, I _{B1} =I _{B2} =1mA			225	
Fall time	t _f				75	
Collector output capacitance	C _{ob}	V _{CB} = 5 V, I _E = 0, f=1MHz			4	pF
Collector input capacitance	C _{ib}	V _{EB} =0.5V, I _E =0, f=1MHz			8	
Transition frequency	f _T	V _{CE} = 20V, I _C = 10mA, f=100MHz	300			MHz

Note.1: Pulse test: pulse width $\leq$ 300 μ s, duty cycle $\leq$ 2 %.

■ Marking

Marking	K2N
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■ Typical Characteristics

